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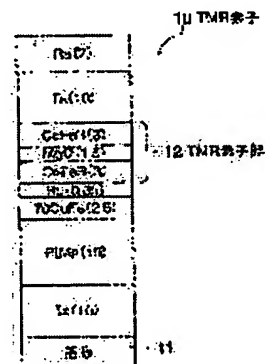
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(54) MAGNETORESISTIVE EFFECT ELEMENT AND ITS MANUFACTURING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a magnetoresistive effect element which is superior in MR ratio and of which mass-productivity and practicality are improved, and to provide its manufacturing method.

SOLUTION: The magnetoresistive effect element (TMR element 10) has a lamination structure (TMR element 12) which is formed of a pair of ferromagnetic layers and a barrier layer located at the middle position between them. At least one ferromagnetic layer is provided with such a portion in contact with the barrier layer that has an amorphous state, and the barrier layer is an MgO layer with a single crystal structure.



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